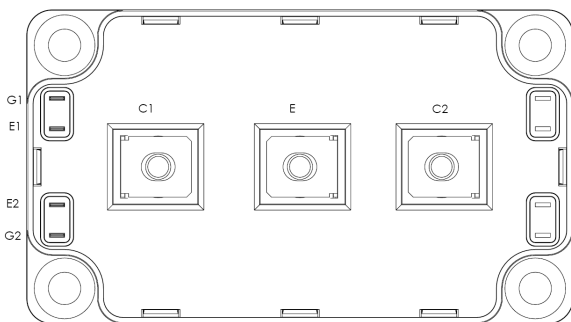
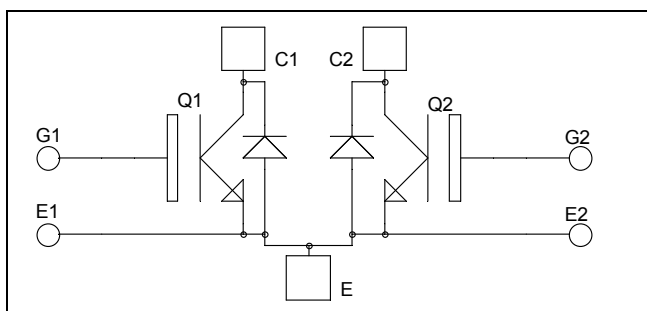


## Dual Common Source NPT IGBT Power Module

**$V_{CES} = 1200V$**   
 **$I_C = 300A @ T_c = 80^\circ C$**



### Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

### Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_c$  of  $V_{CEsat}$
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	400
		$T_c = 80^\circ C$	300
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	600
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1780
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	600A @ 1200V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

### Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			500 750	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		3.3 4	3.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 12mA$		4.5		6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				$\pm 1$	$\mu\text{A}$

### Dynamic Characteristics

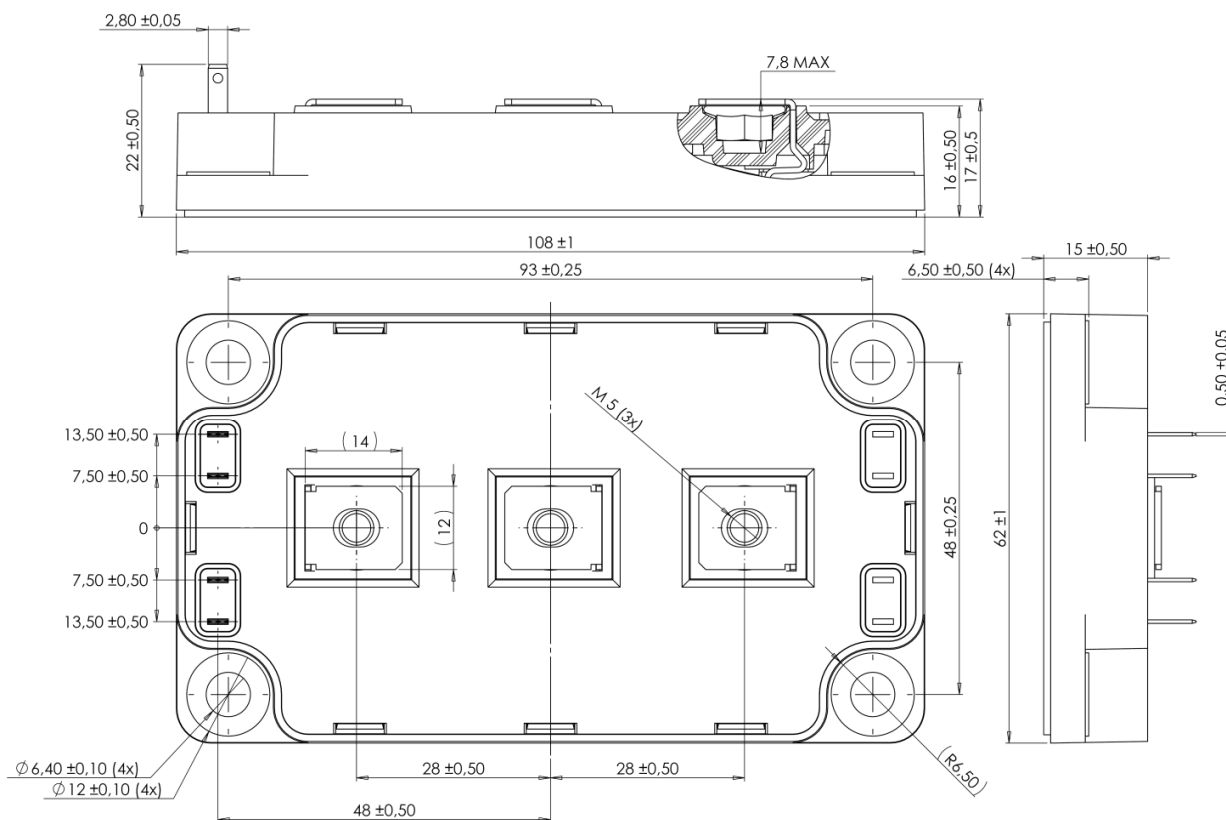
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$			21		nF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			2.9		
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$			1.52		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ )			120		ns
$T_r$	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 300A$			310		
$T_f$	Fall Time	$R_G = 3\Omega$			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ )			130		ns
$T_r$	Rise Time	$V_{GE} = 15V$			60		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 300A$			360		
$T_f$	Fall Time	$R_G = 3\Omega$			40		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125^\circ\text{C}$		25		mJ
$E_{off}$	Turn-off Switching Energy	$I_C = 300A$ $R_G = 3\Omega$	$T_j = 125^\circ\text{C}$		15		

### Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			250 500	$\mu\text{A}$
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$		300		A
$V_F$	Diode Forward Voltage	$I_F = 300A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		2.1 1.9		V
$t_{rr}$	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$ $di/dt = 4500A/\mu s$	$T_j = 25^\circ\text{C}$		120		ns
			$T_j = 125^\circ\text{C}$		210		
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		22		$\mu\text{C}$
			$T_j = 125^\circ\text{C}$		43		
$E_r$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		7 15		mJ

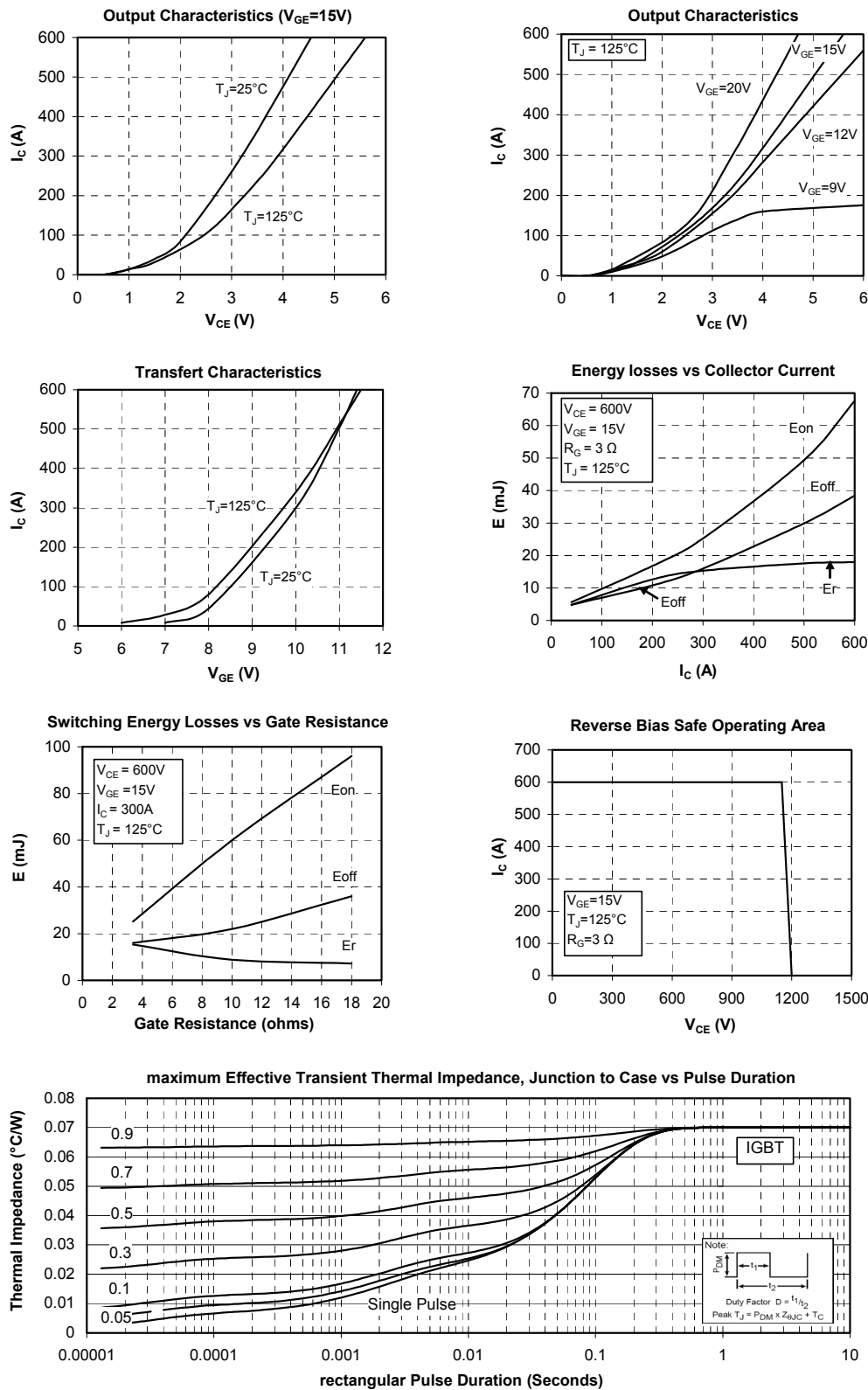
**Thermal and package characteristics**

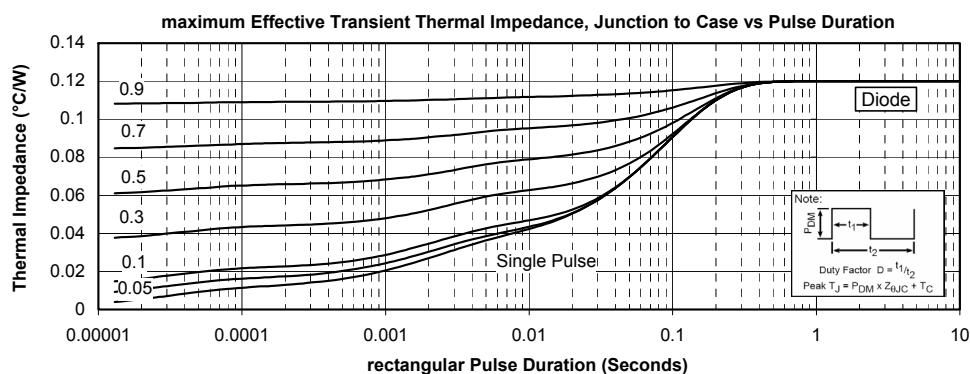
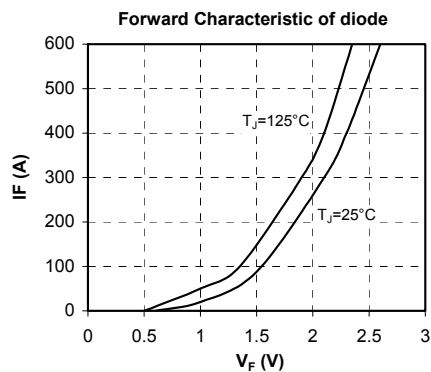
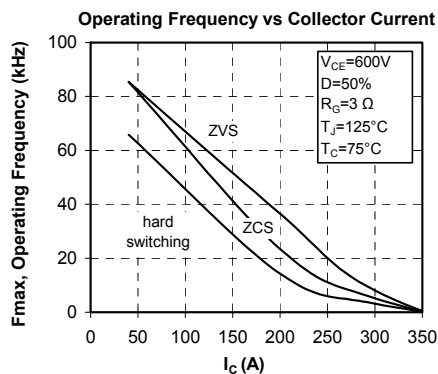
Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT			0.07	°C/W
		Diode			0.12	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz		4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

**SP6 Package outline (dimensions in mm)**


See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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